



>>Entry Name: Antimony sulfide (Sb₂S₃), 9Cl, 8Cl

Synonym(s): Diantimony trisulfide. Antimony(III) sulfide. Antimony trisulfide (incorr.). Gray antimony. Antimonous sulfide. Lupus metallorum

CAS Registry Number: 1345-04-6

Sb₂S₃

Molecular Formula: S₃Sb₂

Molecular Weight: 339.698

Accurate Mass: 337.723852

Percentage Composition: S 28.32%; Sb 71.68%

General Statement: Struct. comprises (Sb₄S₆)_x chains linked to form crumpled sheets. Sb(III) atoms are each bonded to 3 sulfur atoms at corners of basal plane of sl. distorted trigonal pyramid with Sb-S 252.1, 253.9 pm. Other sulfur atoms are at 311.1-364.2 pm from Sb. A Sb(V) atom is below the centre of the basal plane of a distorted sq. pyramid and is bonded to 5 sulfur atoms at the corners of the sq. pyramid. Sb-S 245.5-285.4 pm. May exist as crystalline or amorphous forms

Source/Synthesis: Synth. from Sb + S; or from SbX₃ + thiourea

Use/Importance: Used in photoelectric devices, electrophotographic recording materials

Melting Point: Mp 563°

Boiling Point: Bp 1150°

Other Data: Sol. Na₂S soln. Stable at pH 3-8, and up to 450-500°. Ferroelectric semiconductor. Oxid. to Senarmontite (Sb₂O₃) by *Thiobacillus ferroxidans*. ΔH_f° -141.8 kJ mol⁻¹

Aldrich: 24456-2

Fluka: 10786

>>Variant: Mineral-form

Synonym(s): Stibnite. Antimonite. Platyophthalmite

CAS Registry Number: 1317-86-8

Molecular Formula: S₃Sb₂

Molecular Weight: 339.698

Percentage Composition: S 28.32%; Sb 71.68%

Source/Synthesis: Associated with Au ores. Occurs in parts of the USSR, North Africa, China, Europe (Italy, Bulgaria, Czechoslovakia)

References:

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